

MMBT6428



NPN General Purpose Amplifier

- This device designed for general pupose amplifier applications at collector currents to 300mA
- Sourced from process 10.



MMBT6428

1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings* T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	50	V
V _{CBO}	Collector-Base Voltage	60	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characteristics					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$	50		V
V _{(BR)CBO}	Collector-Base BreakdownVoltage	$I_{\rm C} = 100\mu A, I_{\rm E} = 0$	60		V
I _{CEO}	Collector Cut-off Current	$V_{CE} = 30V, I_B = 0$		0.1	μΑ
I _{CBO}	Collector Cut-off Current	$V_{CB} = 30V, I_E = 0$		10	nA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5.0V, I_B = 0$		10	nA
On Characte	eristics				
h _{FE}	DC Current Gain	$\begin{array}{l} V_{CE} = 5.0V, \ I_{C} = 10\mu A \\ V_{CE} = 5.0V, \ I_{C} = 100\mu A \\ V_{CE} = 5.0V, \ I_{C} = 1.0m A \\ V_{CE} = 5.0V, \ I_{C} = 10m A \end{array}$	250 250 250 250	650	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_{C} = 10mA, I_{B} = 0.5mA$ $I_{C} = 100mA, I_{B} = 5.0mA$		0.2 0.6	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 5.0V, I_{C} = 1.0mA$	0.56	0.66	V
Small Signa	I Characteristics				
f _T	Current gain Bandwidth Product	$V_{CE} = 5.0V, I_{C} = 1.0mA,$ f = 100MHz	100	700	MHz
C _{obo}	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1.0MHz$		3.0	pF
C _{ibo}	Input Capacitance	V _{EB} = 0.5V, I _C = 0, f = 1.0MHz		8.0	pF

*Pulse Test: Pulse Width $\leq 300~\mu s,~\text{Duty}~\text{Cycle} \leq 2.0\%$

Thermal Characteristics T _A =25°C unless otherwise noted						
Symbol	Parameter	Max.	Units			
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C			
$R_{\theta JC}$	Thermal Resistance, Junction to Case		°C/W			
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	357	°C/W			
Device mounted o	n FR-4 PCB 1.6" X 1.6" X 0.06."	•	•			

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